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L. Spruel

IR-1677 (2-1984)

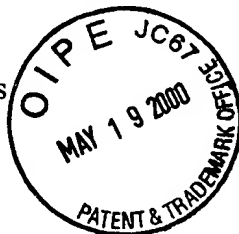
IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of
Zhijun Qu and Kenneth Wagers

Serial No.: 09/329,156

Filed: June 9, 1999

For: DUAL EPITAXIAL LAYER FOR HIGH VOLTAGE VERTICAL
CONDUCTION POWER MOSFET DEVICES



New York, New York

Date: May 15, 2000

Group Art Unit: 2811

Examiner: S. Hu

Asst. Commissioner for Patents
Washington, D.C. 20231

AMENDMENT

Sir:

In response to the Office Action mailed February 16, 2000, please reconsider the
above-identified application amended as follows:

IN THE CLAIMS:

Please amend the claims as follows:

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TC 2800 MAIL ROOM

1. (Amended) A semiconductor device comprising, in combination, a silicon substrate having a first and second surface; a first [epitaxially deposited] layer of epitaxial silicon formed atop said first surface and having impurities of the n or p conductivity type uniformly distributed throughout the volume of said first layer; a second [epitaxially deposited] layer of epitaxial silicon formed [deposited] atop the surface of said first layer and coextensive therewith having impurities of the same type as those in said first layer uniformly distributed therethrough; the concentration of impurities in said second layer being greater than the concentration of impurities in said first layer; and a plurality of diffusions of a conductivity type opposite to that of said second layer uniformly distributed into the surface of said second layer and defining p-n junctions therein.